

1200V SiC Schottky Diode

FEATURES

- Low Conduction and Switching Loss
- Positive Temperature Coefficient on VF
- Temperature Independent Switching Behavior
- Fast Reverse Recovery
- High Surge Current Capability
- Pb-free lead plating

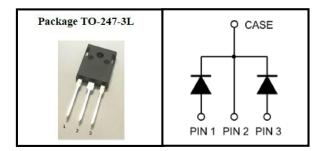
BENEFITS

- Higher System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation
- Hard Switching & High Reliability
- Environmental Protection

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Solar/ Wind Renewable Energy
- Power Inverters
- Motor Drives





Device Marking and Package Information			
Device	Package	Marking	
C2S120E040B	TO-247-3L	C2S120E040B	

Absolute Maximum Ratings T _C = 25°C, unless otherwise noted				
Parameter	Symbol	Test Conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	T _J = 25°C	1200	V
Peak Reverse Surge Voltage	V_{RSM}	$T_{J} = 25^{\circ}C$	1200	V
DC Blocking Voltage	V_R	$T_J = 25^{\circ}C$	1200	V
Continuous Forward Current	l _F	T _J ≤ 135°C	20*	Α
Repetitive Peak Forward Surge Current	I _{FRM}	$T_C = 25^{\circ}C$, $T_P = 8.3$ ms Half Sine Wave	150*	Α
Maximum Case Temperature	T _C		135	°C
Operating Junction and Storage Temperature	$T_J,\;T_stg$		-55~175	°C

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	0.62	°C/W	



Specifications T _J = 25°C, unless otherwise noted					
Parameter	Symbol	Test Conditions	Value		l lasit
			Тур.	Max.	Unit
Converd Voltage	M	$I_F = 20A, T_J = 25^{\circ}C$	1.53	1.7	V
Forward Voltage	V _F	I _F = 20A, T _J = 175°C	2.2	2.5	V
Reverse Current	I _R	V _R =1200V, T _J = 25°C	2	20	μΑ
		V _R =1200V, T _J = 175°C	20	100	μΑ
Total Capacitive Charge	Q _C	I _F = 20A, di/dt =200A /μs V _R =1200V, T _J = 25°C	70		nC
		V _R =0V, T _J = 25°C, , f =1 MHz	1260		
Total Capacitance	С	V _R =400V, T _J = 25°C, , f =1 MHz	80		pF
		V _R =800V, T _J = 25°C, , f =1 MHz	73		



Device Performances

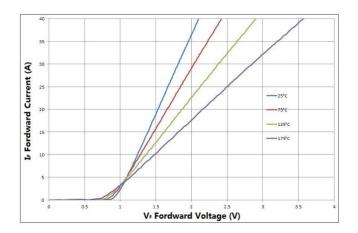


Fig. 1 Forward Characteristics

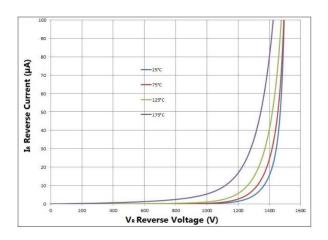


Fig. 2 Reverse Characteristics

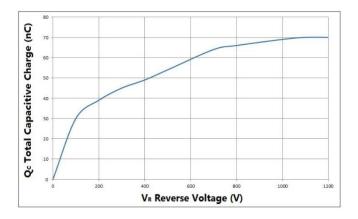


Fig. 3 Total Capacitance Charge vs. Reverse Voltage

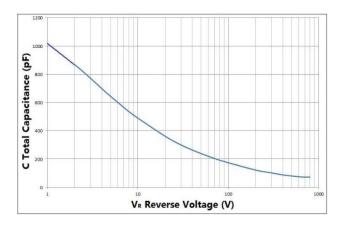


Fig. 4 Total Capacitance vs. Reverse Voltage

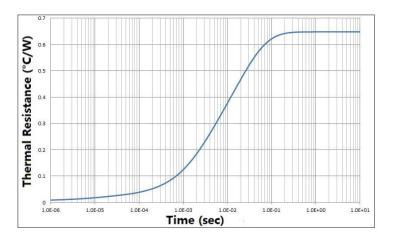
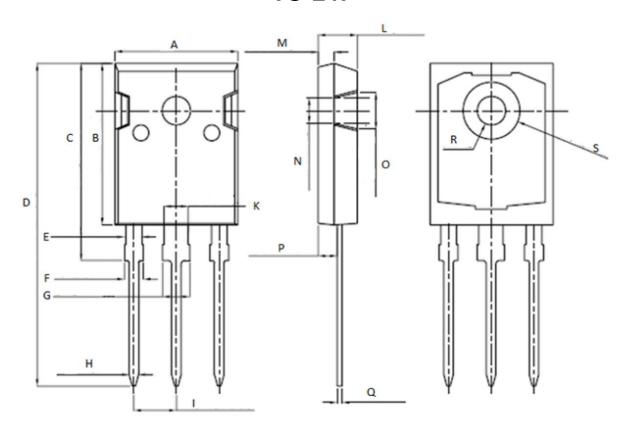


Fig. 5 Transient Thermal Impedance



TO-247



Unit: mm			
Symbol	Min.	Max.	
Α	15. 95	16. 25	
В	20. 85	21. 25	
С	20. 95	21. 35	
D	40. 5	40. 9	
E	1. 9	2. 1	
F	2. 1	2. 25	
G	3. 1	3. 25	
Н	1.1	1. 3	
I	5. 40	5. 50	

Unit: mm			
Symbol	Min.	Max.	
K	2. 90	3. 10	
L	4. 90	5. 30	
M	1. 90	2. 10	
N	4. 50	4. 70	
0	5. 40	5. 60	
Р	2. 29	2. 49	
Q	0. 51	0. 71	
R	ф 3. 5	ф 3. 7	
S	ф 7. 1	ф 7. 3	



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